# **Topic 4 : Cleanroom laboratory**

The objective of this cleanroom session is:

- to familiarize students with the cleanroom environment, equipment, and safety rules.
- To handle correctly wafers and masks until the end of the fabrication sequence. The wafer must be handled with the appropriate wafer tweezers and with great attention. Never touch the surface of the wafer, even with gloved hands.
- To practice alignment between two levels
- To do a wet etching process of aluminum film
- To prepare a photomask
- To learn the behavior in the cleanroom
- To prepare and use a process flow

Important: During your session, follow the process descriptions and details provided by your TA. You should take notes of the explanation given by your TA to be added in your final report to explain all procedures you have performed in the cleanroom.

# 1. Entering the cleanroom

- Sit down on the bench.
- Put on plastic overshoes normally available close to the bench.
- Get a cleanroom suit to your size. When dressing, make sure that the sleeves do not touch the floor.
- Put on boots/cleanroom shoes.
- Put on a cleanroom mask and a hair net.
- Put on safety goggles (if no medical glasses).
- Put on gloves.
- Check if you are well dressed up before entering in the cleanroom.

#### 2. Photomask fabrication

The photomask is a solid, transparent substrate, such as glass or fused silica, which has an opaque coating on one surface into which a microscopic pattern has been etched, leaving some regions transparent and others opaque. Light can pass through the mask only from the transparent regions. When the photomask is placed in proximity to another substrate coated with photosensitive material called photoresist, only the light that travels through the photomask will irradiate the photoresist.

- Your photomask is created by designing patterns using CAD (Computer Aided Design) tools, such as Klayout (free software), and a gds file is generated.
- Laser writer VPG200 has been used to write this file on the photoresist of the photomask.
- With your TA, you will continue the rest of the process: development of the photoresist, Chrome etch, and resist stripping. Hamatech HMR900 is a tool dedicated to Cr-plate wet processing or cleaning. Three dedicated media are installed for

successive chemical treatment of standard Cr-blanks (developing exposed resist – Cr wet etching – resist striping) with intermediate DI water rinse and final drying. The tool is designed to handle square plates up to 7" x 7" (Cr-blank for mask aligner or reticule for DUV stepper)

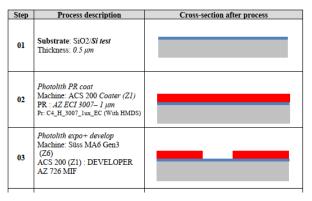
## 3. SiO<sub>2</sub> Film Formation and Mask Alignment

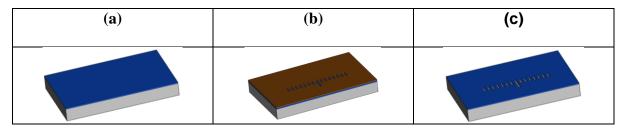
You need:

- PR/ SiO<sub>2</sub>/Si wafer
- Mask level 2

A  $SiO_2$  film is formed through the oxidation of a silicon wafer, resulting in a film thickness of 100 nm. This oxidation process can occur in a high-temperature oven, where silicon reacts with oxygen to create a thermal oxide layer

To transfer the initial designs onto the  $SiO_2$  film (a), mask level 1 is used. This involves applying a photolithographic process where a photoresist is patterned onto the  $SiO_2$  layer. The unprotected areas of the film are then selectively removed using a Buffered Oxide Etch (BOE) (c). BOE is a specialized etching solution that typically contains a mixture of ammonium fluoride and hydrofluoric acid, which effectively etches silicon dioxide. The careful control of the etching parameters ensures that the desired features are accurately transferred.



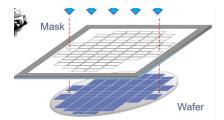


Task: Aligning Mask Level 2

Your objective is to align Mask Level 2 with high precision relative to Level 1.

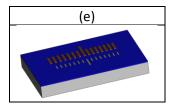
- Preparation: Ensure that the Süss MA6 Gen3 mask aligner machine is set up according to the specifications provided by your Teaching Assistant (TA).
- Start by loading the mask onto the contact aligner mask stage. Turn on the mask vacuum and raise the mask stage.

- Loading the wafer on the center of the wafer holder, the photoresist side facing up to the photomask. Turn on the substrate vacuum to fix the substrate in place.
- perform a wedge error compensation (WEC). This step ensures that the sample is parallel to the photomask.
- Align the mask to the wafer using the alignment marks on the sides of the wafer and the mask. The mask aligner has two objectives allowing the user to view both alignment marks simultaneously. The image seen is split in half with the left image corresponding to one location of the substrate and the right half corresponding to another location of the substrate.



- Alignment is achieved by adjusting the x, y, and  $\theta$  (theta) positions of the wafer in relation to the stationary mask. This process is crucial for ensuring that the patterns on Mask Level 2 accurately overlay those on Mask Level 1.
- After finishing the alignment, expose your wafer to UV light. The exposure time must be previously determined from the datasheet of the used photoresist. During the exposure, make sure you turn away from the UV light to protect yourself from the UV exposure.
- Automatic development step involves a systematic procedure that includes developing the wafer in MIF726 developer, followed by a thorough water rinse, and finally, a nitrogen (N2) drying process.

After the UV exposure and development process, your substrate will consist of three distinct materials: Si Wafer, thin  $SiO_2$  film, and a photoresist layer. The schematic below (e) illustrates a vernier designed for measuring alignment errors. This tool is essential for ensuring that the patterns transferred onto the substrate are accurately aligned, which is critical for the performance of the final device. Understanding these alignment errors will be further explored in Topic 6, where detailed methodologies for measurement and evaluation will be discussed.



## 4. Aluminium Etching.

For this exercice you need:

- PR/AI/Glass substrate
- Your mask you have prepared

### Steps to follow:

• The process flow for this exercise is below

Step	Process description	Cross-section after process
01	Substrate: Al/Glass Thickness: 0.8 µm	
02	Photolith PR coat Machine: ACS 200 Coater (Z1) PR: AZ ECI 3007—1 µm Pr: C4_D_3007_lux_EC (Without HMDS)	
03	Photolith expo+ develop Machine: Süss MA6 Gen3 (Z6) ACS 200 (Z1): DEVELOPER AZ 726 MIF	
04	Wet Etch Material : Al (Z2) Plade metal : APN depth : 0.8 μm	
05	Resist Strip Material: AZ ECI 3007– 1 µm (Z2) Bain remover 1165	

- Load the mask you have prepared with your assistant on the Süss MA6 Gen3 mask aligner. Load the PR/Al/Glass substrate on the machine. No alignment is required. Contact and expose to UV light for the right exposure time.
- The exposure time is determined with your TA and also you take note of the manner of determining this time to be included in your final report.
- Automatic development step involves a systematic procedure that includes developing the wafer in MIF726 developer, followed by a thorough water rinse, and finally, a nitrogen (N2) drying process.
  - Aluminum etching, this step should be carried out by the lab TA for safety reasons.
    The exposed aluminum film is removed in APN a mixture of three acids: Acetic,
    Phosphoric, and Nitric. It etches aluminum at approximately 300 nm/min and is
    highly selective to aluminum compared to photoresist.
- Photoresist stripping
  - Can be done manually, or in plasma oxygen

### 5. Aluminum Thickness Measurements

- i. Measure the thickness of the patterned aluminum film with the Stylus Profilometer
- 6. Store your wafers in their containers until the characterization session (topic 6).

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#### What is a cleanroom?

 ${\bf Clean room\ environment\ requires\ special\ cloth,\ compatible\ tools,\ lint\ free\ paper.}$ 

 Body may contaminate by: Flakes of dead skin Hair Touch by hand Breathing

Wrong cloth may release:

Dust

Wrong tools may create:

Particles Dust









CMi Diri Carter of EPFL Safety rules: chemistry

- INFORM yourself (SDS).
- Do NOT crowd fume hoods/wet
- Only ONE user at a time for "strong" chemistry (concentrated acids/bases).
- Do NOT stress operator for quick finish.
- Finish clean and safe (workplace, bottles, wares...)

# Extra dressing

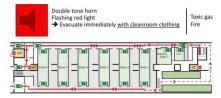
- nitrile gloves safety apron
- face shield
- long gloves



CMi (N) Contact of

EPFL

Safety rules: alarms & Evacuation in CMi BM -1 / Z18-19



Meeting point : BM 1.124 (CMi secretariat office) wait there to be accounted for

Remark : red alarm can be activated by the push-buttons

Safety rules: general

CMI (M) Corner of EPFL

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CAMIPRO required for each person entering or leaving the cleanroom Never work alone: a buddy is required in the cleanroom at all times Only one emergency phone number :

Report any safety problems you encounter Wear protective glasses or medical glasses all the time

## EPFL

#### Cleanroom general rules

- Material should be stored in labelled basket
- All wafers should be in boxes with :
- Labelled owner and date
   Ideally with process flow in snap-on clear envelopes

Lost and found shelf









